

Dual N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

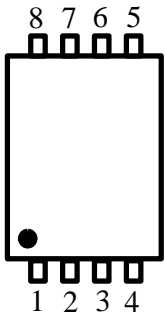
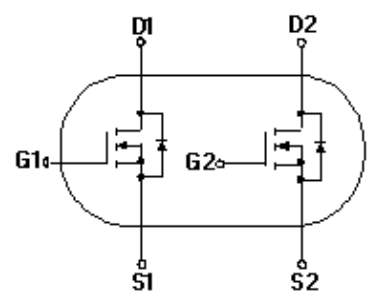
1.2 Applications

- Motor drivers
- DC - DC Converter

1.3 Quick reference

- $BV \geq 60\text{ V}$
- $R_{DS(ON)} \leq 14\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 35\text{ W}$
- $R_{DS(ON)} \leq 27\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- $I_D \leq 39\text{ A}$

2. Pin Description

| Pin | Description | Simplified Outline | Symbol |
|-----|-------------|---|---|
| 1 | Source(S1) |  <p style="text-align: center;">Top View DFN5x6-8L</p> |  |
| 2 | Gate(G1) | | |
| 3 | Source(S2) | | |
| 4 | Gate(G2) | | |
| 5,6 | Drain(D2) | | |
| 7,8 | Drain(D1) | | |

3. Limiting Values

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------------|---|---|------|------|--------|
| V _{DS} | Drain-Source Voltage | T _C = 25 °C | 60 | - | V |
| V _{GS} | Gate-Source Voltage | T _C = 25 °C | - | ± 20 | V |
| I _D * | Drain Current (DC) | T _C = 25 °C, V _{GS} = 10 V | - | 39 | A |
| | | T _C = 100 °C, V _{GS} = 10 V | - | 25 | A |
| I _{DM} *,**,*** | Drain Current (Pulsed) | T _C = 25 °C, V _{GS} = 10 V | - | 120 | A |
| P _{tot} * | Total Power Dissipation | T _C = 25 °C | - | 35 | W |
| T _{stg} | Storage Temperature | | - 55 | 150 | °C |
| T _J | Junction Temperature | | - | 150 | °C |
| I _S | Diode Forward Current | T _C = 25 °C | - | 39 | A |
| E _{AS} * | Single Pulsed Avalanche Energy | V _{DD} = 50 V , L= 1.0 mH | - | 60.5 | mJ |
| R _{θJA} * | Thermal Resistance- Junction to Ambient | | - | 62.5 | °C / W |
| R _{θJC} * | Thermal Resistance- Junction to Case | | - | 3.5 | |

Notes :

- * Surface Mounted on 1 in² pad area, t ≤ 10 sec
- ** Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- *** Limited by bonding wire

4. Marking Information

| Product Name | Marking |
|--------------|--|
| KJ12D06GM | 12D06M YWW : YWWXXX Date Code |

5. Ordering Code

| Product Name | Package | Reel Size | Tape width | Quantity | Note |
|--------------|---------|-----------|------------|----------|------|
| KJ12D06GM | PDFN5*6 | | | 5000 | |

Note: KUAJIEXIN defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

6. Electrical Characteristics (T_A = 25 °C Unless Otherwise Noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--|----------------------------------|---|-----|------|-------|------|
| Static Characteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0 V, I _D = 250 μA | 60 | - | - | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _{DS} = 250 μA | 1 | - | 3 | V |
| I _{DSS} | Zero Gate Voltage Source Current | V _{DS} = 48 V, V _{GS} = 0 V | - | - | 1 | μA |
| I _{GSS} | Gate Leakage Current | V _{GS} = ± 20 V, V _{DS} = 0 V | - | - | ± 100 | nA |
| R _{DS(ON)} ^a | Drain-Source On-State Resistance | V _{GS} = 10 V, I _D = 10 A | - | 12.3 | 14 | mΩ |
| | | V _{GS} = 4.5 V, I _D = 5 A | - | 21.3 | 27 | |
| Diode Characteristics | | | | | | |
| V _{SD} ^a | Diode Forward Voltage | I _{SD} = 10 A, V _{GS} = 0 V | - | - | 1.3 | V |
| t _{rr} | Reverse Recovery Time | I _{SD} = 10 A, dI _{SD} /dt = 100 A/μs | - | 25 | - | nS |
| Q _{rr} | Reverse Recovery Charge | | - | 13 | - | nC |
| Dynamic Characteristics^b | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} = 0 V, V _{DS} = 30 V Frequency = 1 MHz | - | 764 | - | pF |
| C _{oss} | Output Capacitance | | - | 354 | - | |
| C _{rss} | Reverse Transfer Capacitance | | - | 41 | - | |
| t _{d(on)} | Turn-on Delay Time | V _{DS} = 30 V, V _{GEN} = 10 V, R _G = 3.9 Ω, R _L = 3 Ω, I _{DS} = 10 A | - | 6.5 | - | nS |
| t _r | Turn-on Rise Time | | - | 22 | - | |
| t _{d(off)} | Turn-off Delay Time | | - | 14 | - | |
| t _f | Turn-off Fall Time | | - | 4.3 | - | |
| Gate Charge Characteristics^b | | | | | | |
| Q _g | Total Gate Charge | V _{DS} = 30 V, V _{GS} = 10 V, I _{DS} = 10 A | - | 15 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 3.9 | - | |
| Q _{gd} | Gate-Drain Charge | | - | 3.3 | - | |

Notes :

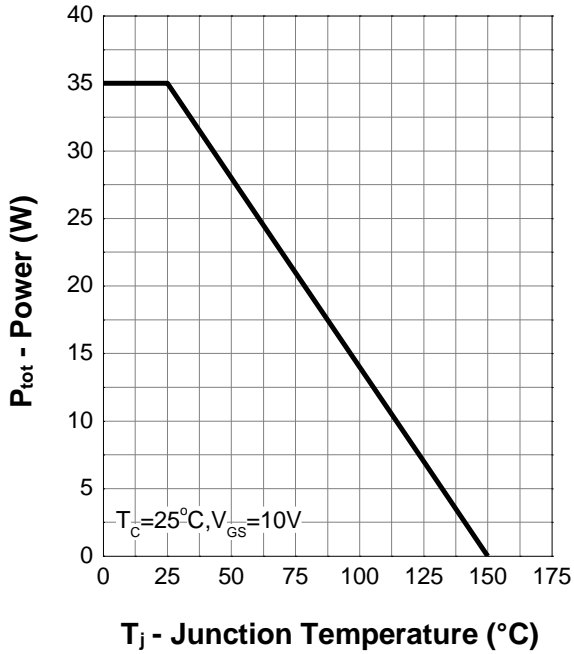
a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b : Guaranteed by design, not subject to production testing

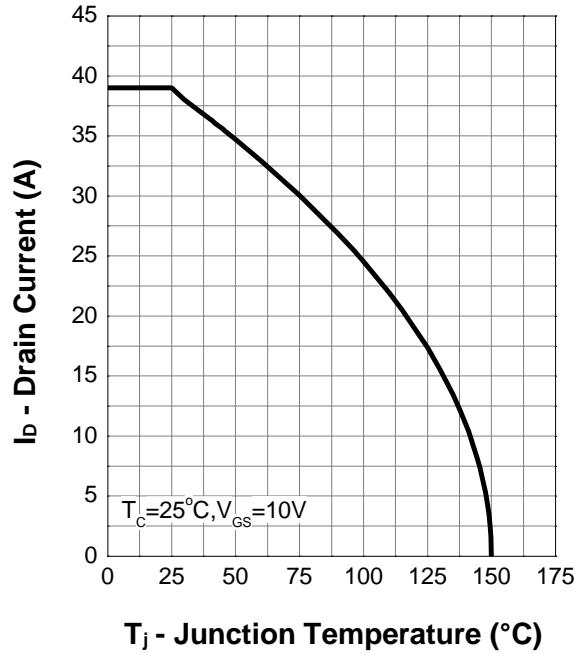


7. Typical Characteristics (Cont.)

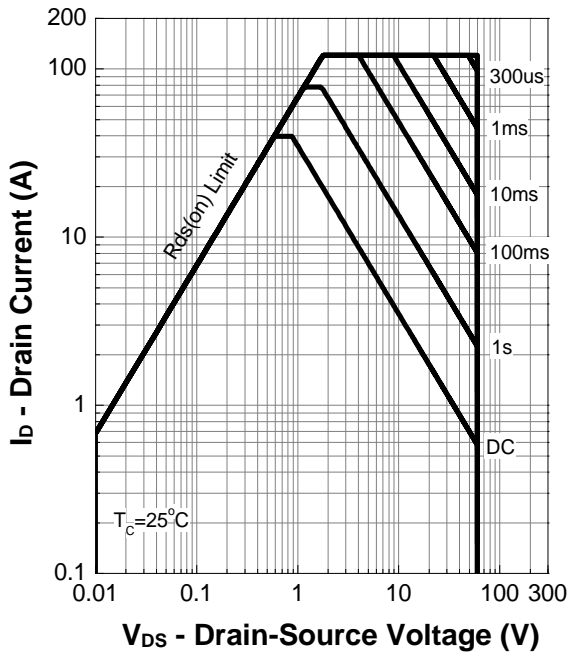
Power Capability



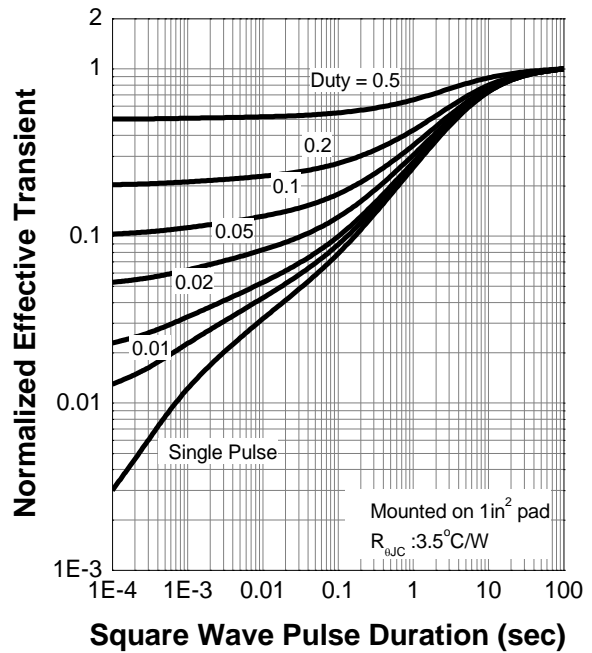
Current Capability



Safe Operation Area



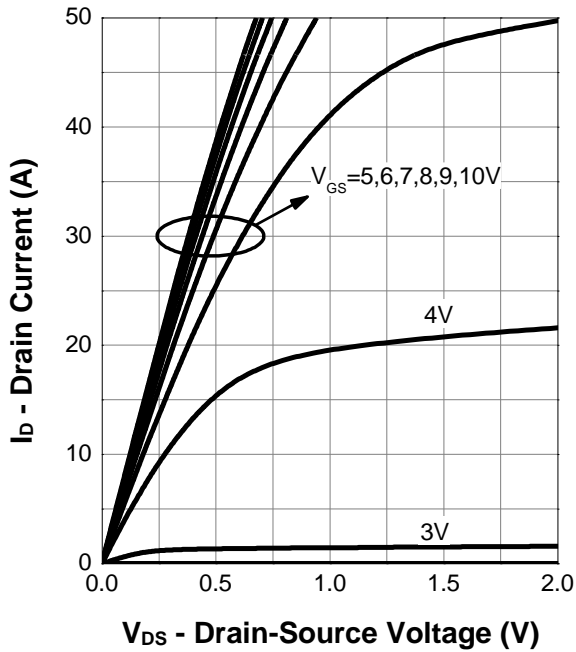
Transient Thermal Impedance



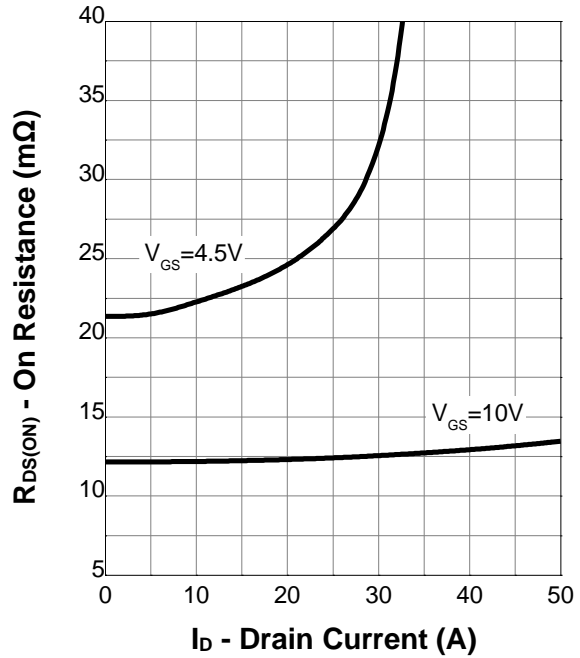


7. Typical Characteristics (Cont.)

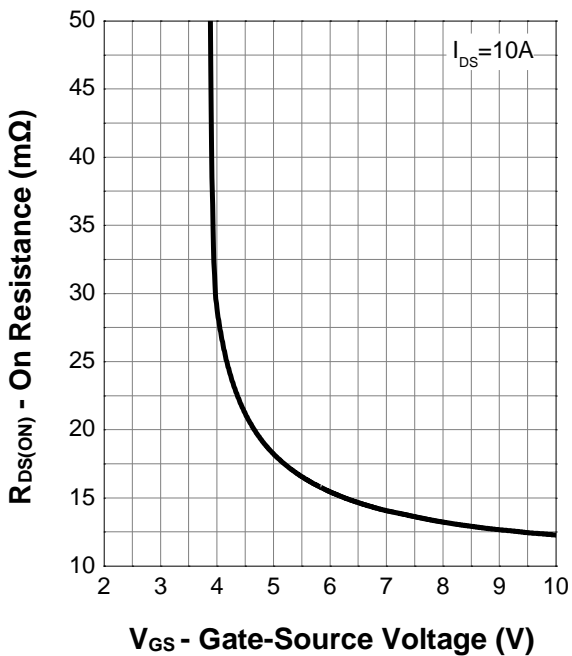
Output Characteristics



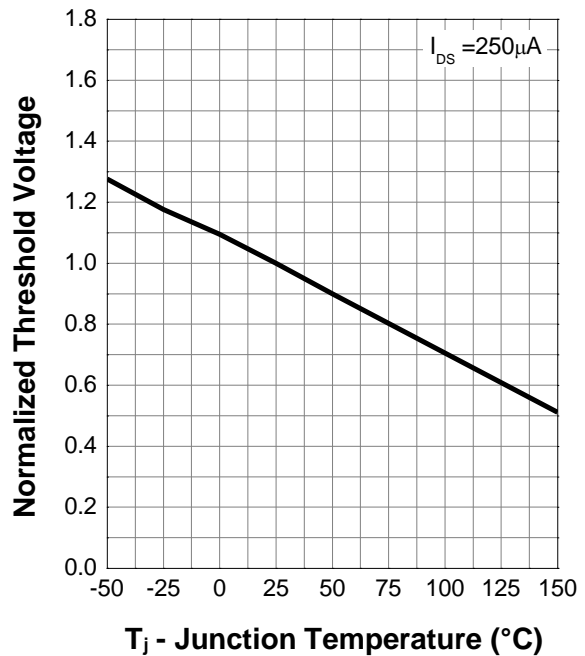
On Resistance



Transfer Characteristics



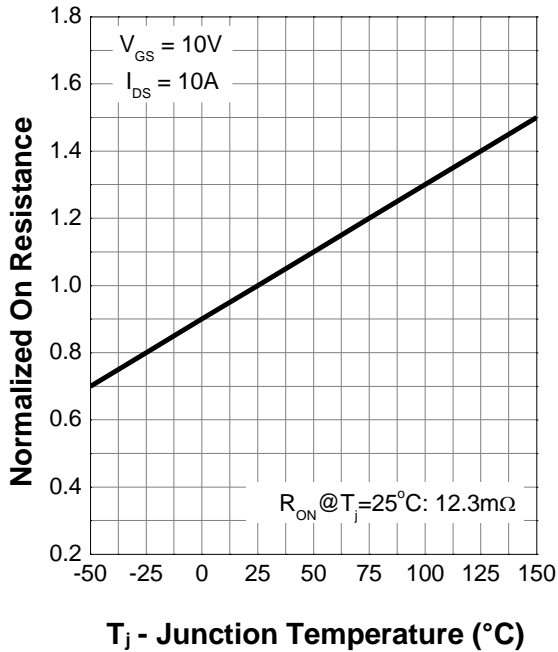
Normalized Threshold Voltage



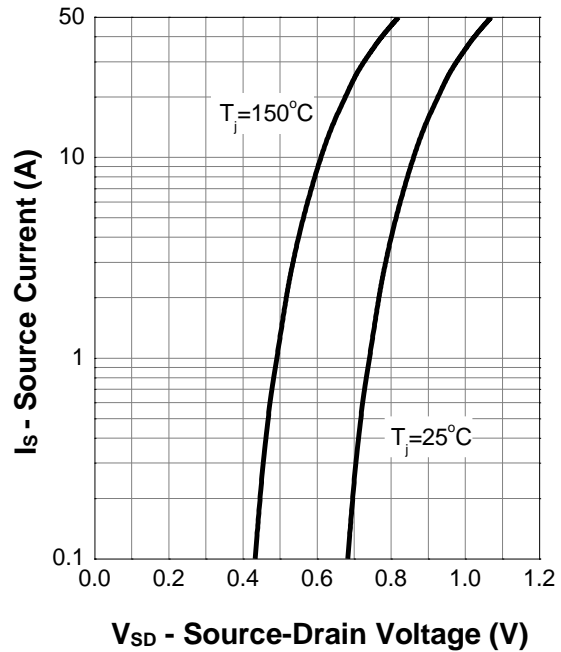


7. Typical Characteristics (Cont.)

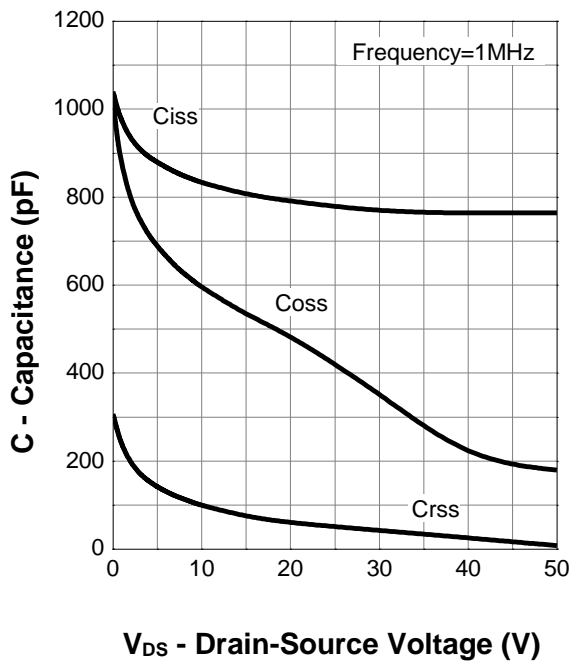
Normalized On Resistance



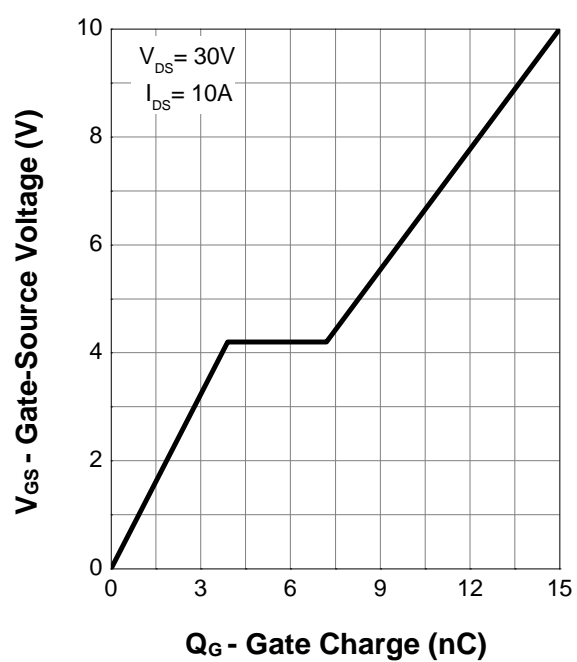
Diode Forward Current



Capacitance



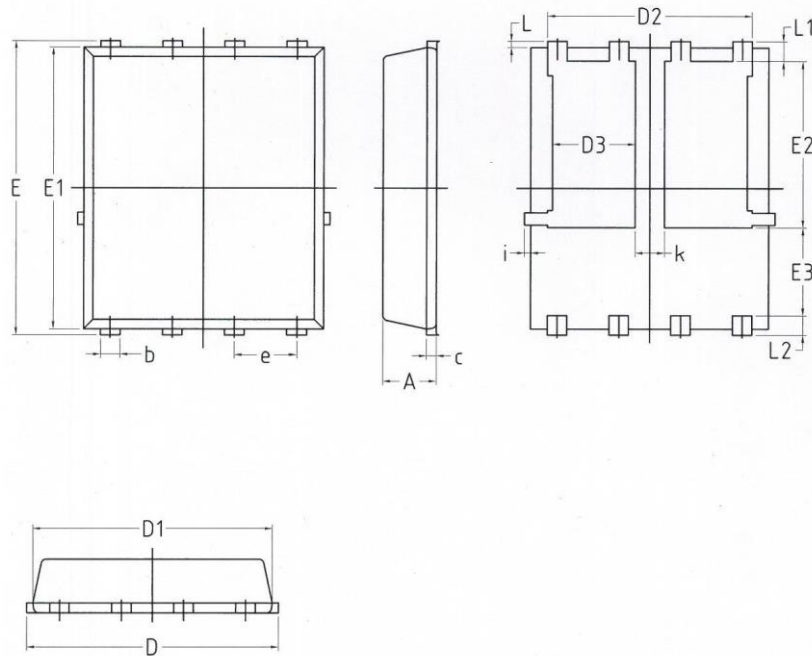
Gate Charge





8. Package Dimensions

DFN5x6 - 8L (Dual) Package



| Symbol | Dimensions In Millimeters | |
|--------|---------------------------|------|
| | MIN. | MAX. |
| A | 1.03 | 1.17 |
| B | 0.34 | 0.48 |
| c | 0.203 BSC | |
| D | 4.8 | 5.4 |
| D1 | 4.8 | 5.0 |
| D2 | 4.11 | 4.31 |
| D3 | 1.6 | 1.8 |
| E | 5.95 | 6.15 |
| E1 | 5.65 | 5.85 |
| E2 | 3.3 | 3.5 |
| E3 | 1.7 | - |
| e | 1.27 BSC | |
| L | 0.05 | 0.25 |
| L1 | 0.38 | 0.5 |
| L2 | 0.38 | 0.5 |
| i | - | 0.18 |
| k | 0.5 | 0.7 |